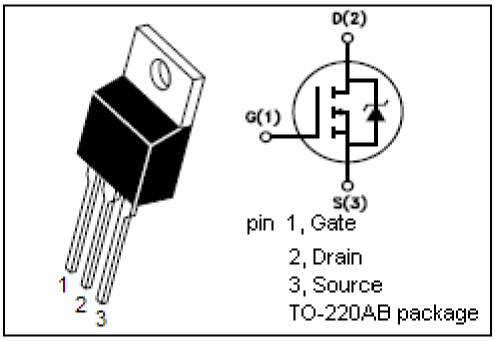
isc N-Channel Mosfet Transistor IRF620FI

• FEATURES

- Low $R_{DS(on)}$
- V_{GS} Rated at ±20V
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements



• DESCRITION

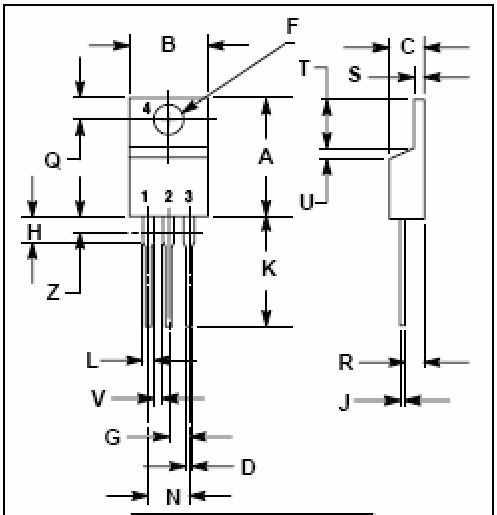
- Designed for high speed applications, such as switching power supplies , AC and DC motor controls,relay and solenoid drivers and other pulse.

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	4	A
I_{DM}	Drain Current-Single Plused	16	A
P_D	Total Dissipation @T_C=25℃	30	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.12	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	80	℃/W



DIM	mm MIN	mm MAX
A	14.48	15.75
B	9.66	10.28
C	4.07	4.82
D	0.64	0.88
F	3.61	3.73
G	2.42	2.66
H	2.80	3.93
J	0.46	0.64
K	12.70	14.27
L	1.15	1.52
N	4.83	5.33
Q	2.54	3.04
R	2.04	2.79
S	1.15	1.39
T	5.97	6.47
U	0.00	1.27
V	1.15	---
Z	---	2.04

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	200		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 3A		0.8	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±500	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 200V; V_{GS}=0		250	uA
V_{SD}	Forward On-Voltage	I_S= 4A; V_{GS}=0		1.8	V